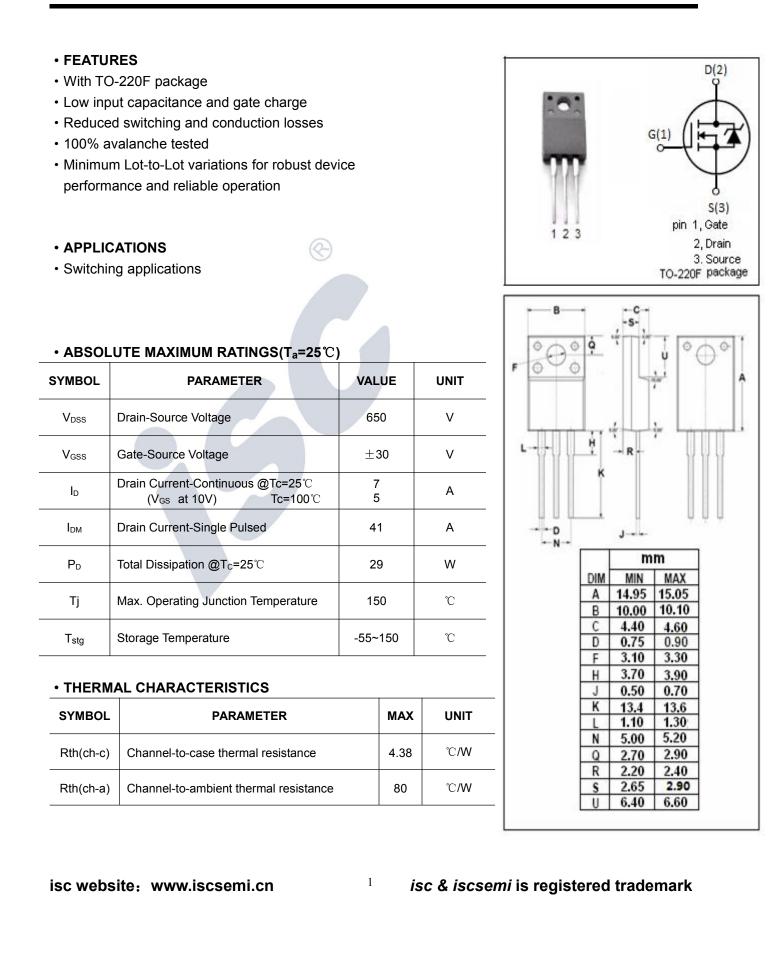


INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

IPA65R225C7





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IPA65R225C7

ELECTRICAL CHARACTERISTICS

$T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|----------------------|--------------------------------|--|-----|-----|----------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =1mA | 650 | | | V |
| V _{GS} (th) | Gate Threshold Voltage | V _{DS} = V _{GS} ; I _D =0.24mA | 3.0 | | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =4.8A | | 199 | 225 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V;V _{DS} = 0V | | | ±0.1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 650V; V _{GS} = 0V;Tj=25℃ V _{DS} = 650V; V _{GS} = 0V; Tj=150℃ | | | 1 100 | μA |
| V _{SDF} | Diode forward voltage | I _{SD} =4.8A, V _{GS} = 0V | | 0.9 | | V |

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